

LATTICE DEFORMATION AND THE SPATIAL  
REDISTRIBUTION OF POINT DEFECTS  
IN A STRESSED EPITAXIAL LAYER

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S u m m a r y

A model of the deformation-diffusion phenomena in stressed epitaxial layers has been constructed on the basis of the self-consistent system of equations for the defect concentration and the deformation parameter. The calculations of the stationary profile of point defects (interstitial atoms and vacancies) and the lattice deformation parameter in InAs epitaxial layers grown on the GaAs substrate have been carried out. The dependence of the deformation parameter on the distance from the heterointerface has been shown nonmonotonous provided that there are point defects in the epitaxial layer.